

BORDERLESS CONTACT STRUCTURES

Abstract

A borderless contact structure and method of fabricating the structure, the method including: (a) providing a substrate; (b) forming a polysilicon line on the substrate, the polysilicon line having sidewalls; (c) forming an insulating sidewall layer on the sidewalls of the polysilicon line; (d) removing a portion of the polysilicon line and a corresponding portion of the insulating sidewall layer in a contact region of the polysilicon line; and (e) forming a silicide layer on the sidewall of the polysilicon line in the contact region. Also an SRAM cell using the borderless contact structure and a method of fabricating the SRAM cell.